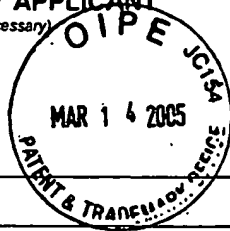


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First Named Inventor	Ahn, Kie
Group Art Unit	2823
Examiner Name	Toledo, Fernando

Attorney Docket No: 1303.101US1

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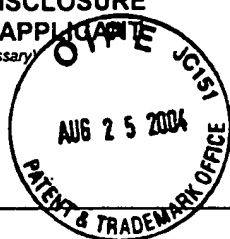
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Group Art Unit	2823
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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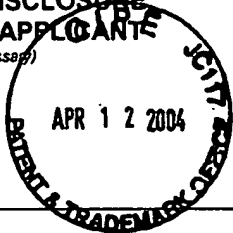
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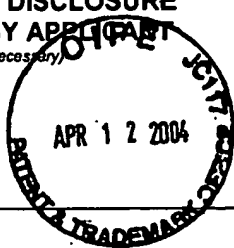
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